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# Publisher Correction: An electrochemical thermal transistor

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Correction to: *Nature Communications* <https://doi.org/10.1038/s41467-018-06760-7>, published online 30 October 2018.

The original version of this Article contained an error in Fig. 2a in which the label on the y-axis incorrectly read ‘Al/MoS<sub>2</sub>OiS/2’ rather than the correct ‘Al/MoS<sub>2</sub>/SiO<sub>2</sub>’.

Further, the original version contained an error in the last sentence of the seventh paragraph of the Discussion which incorrectly read ‘Reducing the temperature swing can have a significant effect on device reliability as the relationship between  $\Delta T$  and the number of cycles to failure  $N_f$  is strongly non-linear<sup>38</sup>,  $N_f \sim \Delta T^{-3,5}$ ’. The correct version states ‘ $\Delta T^{-3,5}$ ’ in place of ‘ $\Delta T^{-3,5}$ ’.

This has been corrected in both the PDF and HTML versions of the Article.

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